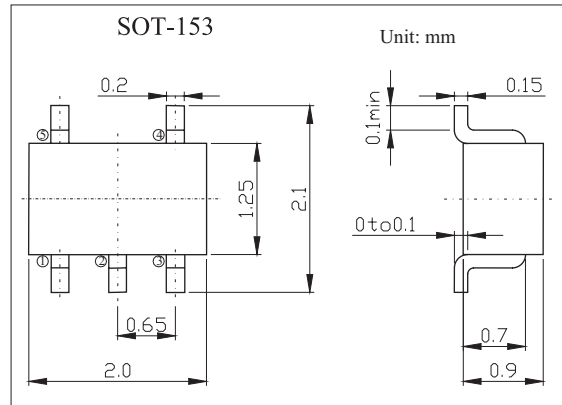
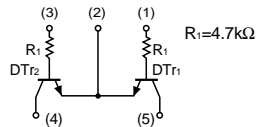


FMG3A

■ Features

- Dual NPN digital transistor



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Power dissipation(Total)	P_d	300	mW
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 50 \mu\text{A}, I_E = 0$	50			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	50			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_C = 50 \mu\text{A}, I_C = 0$	5			V
Collector cutoff current	I_{CBO}	$V_{CB}=50\text{V}, I_E=0$			0.5	μA
Emitter cutoff current	I_{EBO}	$V_{EB}= 4\text{V}, I_C=0$			0.5	μA
DC current gain	h_{FE}	$V_{CE}=5\text{V}, I_C=1\text{mA}$	100	250	600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}$			0.3	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_E= -5\text{mA}, f=100\text{MHz}$		250		MHz
Input resistance	R_1		3.29	4.7	6.11	k Ω

■ Marking

Marking	G3
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■ Typical Characteristics

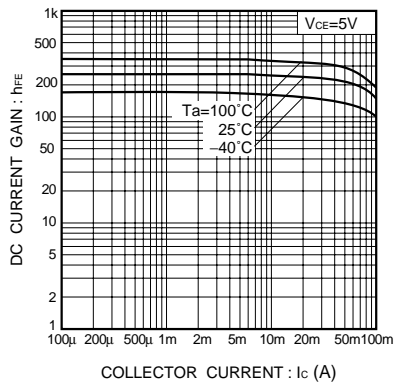


Fig.1 DC current gain vs. collector current

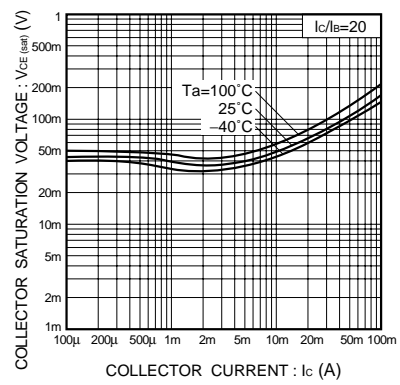


Fig.2 Collector-emitter saturation voltage vs. collector current